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Abstract

The invention concerns a method for making substrates, in particular for optics, electronics or optoelectronics, characterised in that it comprises an operation which consists in implanting (100) atomic species beneath the surface of a material in the form of a cylindrical ingot (1), at a depth of implantation distributed about a certain value by bombardment of said atomic species on a zone of the ingot (1) cylindrical surface, and an operation which consists in removing (300), at a separation depth located proximate to the depth of implantation, the layer (2) of material located between the surface and the separation depth, to remove said layer (2) from the rest of the ingot (1)

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